

<b>SANYO</b>	No.4136	<b>2SC4884</b>
		NPN Epitaxial Planar Silicon Transistor High Definition CRT Display Video Output Applications

**Applications**

- High Definition CRT Display.
- Especially suited for use in Color TV Chrome Output and High Breakdown Voltage Driver Applications.

**Features**

- Adoption of MBIT process.
- Large allowable collector dissipation.
- High breakdown voltage ( $V_{CEO} \geq 300V$ ).
- Excellent high frequency characteristic ( $C_{re} = 1.8pF$  typ).
- Usage of radial taping to meet automatic mounting.

**Absolute Maximum Ratings at  $T_a = 25^\circ C$** 

			unit
Collector-to-Base Voltage	$V_{CBO}$	300	V
Collector-to-Emitter Voltage	$V_{CEO}$	300	V
Emitter-to-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	100	mA
Peak Collector Current	$i_{cp}$	200	mA
Collector Dissipation	$P_C$	1.5	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

**Electrical Characteristics at  $T_a = 25^\circ C$** 

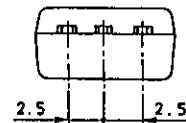
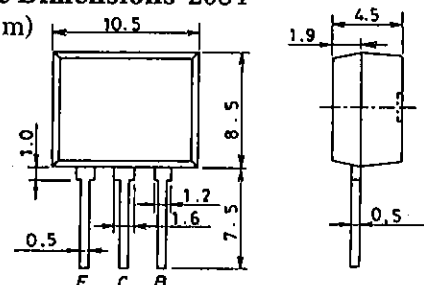
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 200V, I_E = 0$			0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			0.1	$\mu A$
DC Current Gain	$h_{FE}$	$V_{CE} = 10V, I_C = 10mA$	60*		320*	
Gain Bandwidth Product	$f_T$	$V_{CE} = 30V, I_C = 10mA$		70		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = 30V, f = 1MHz$		2.6		pF
Reverse Transfer Capacitance	$C_{re}$	$V_{CB} = 30V, f = 1MHz$		1.8		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 20mA, I_B = 2mA$			0.6	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 20mA, I_B = 2mA$			1.0	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	300			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	300			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5			V

\* : The 2SC4884 is classified by 10mA  $h_{FE}$  as follows :

60	D	120	100	E	200	160	F	320
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**Package Dimensions 2084**

(unit: mm)



E : Emitter  
C : Collector  
B : Base

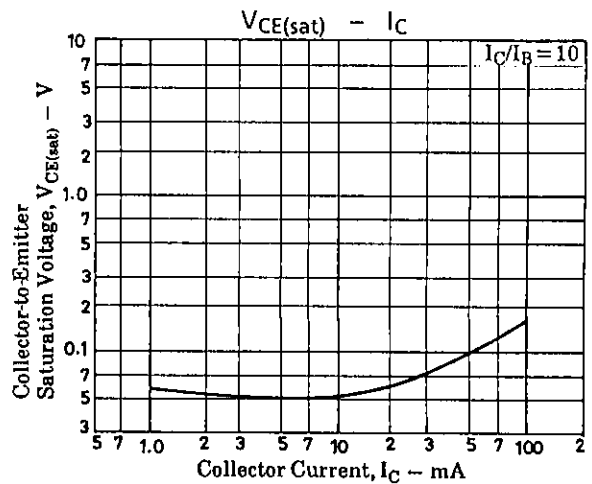
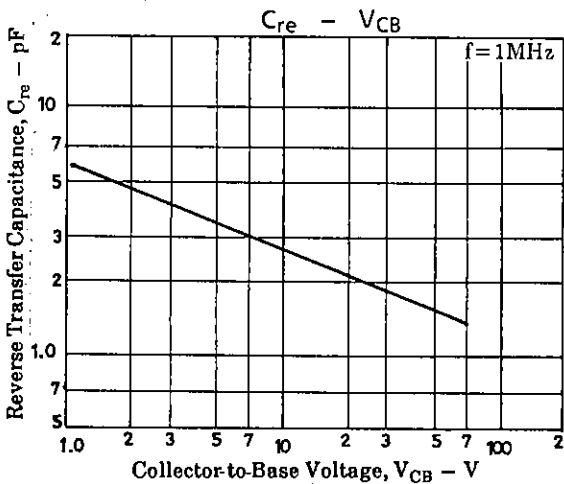
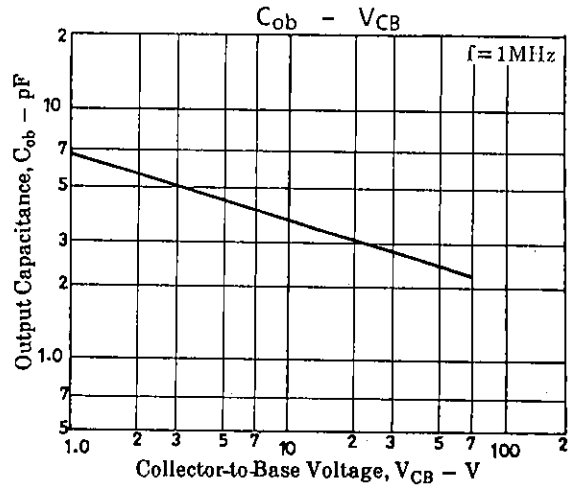
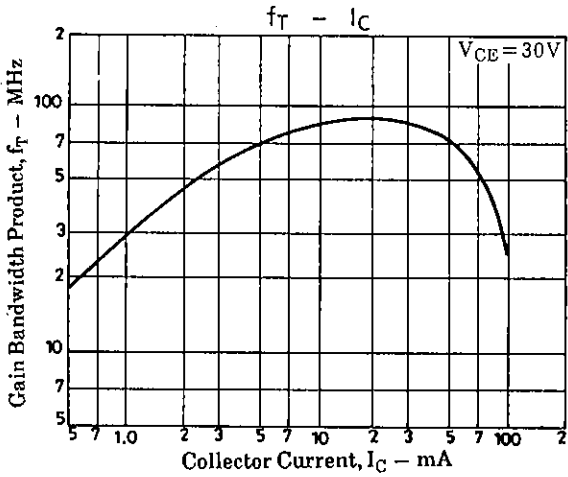
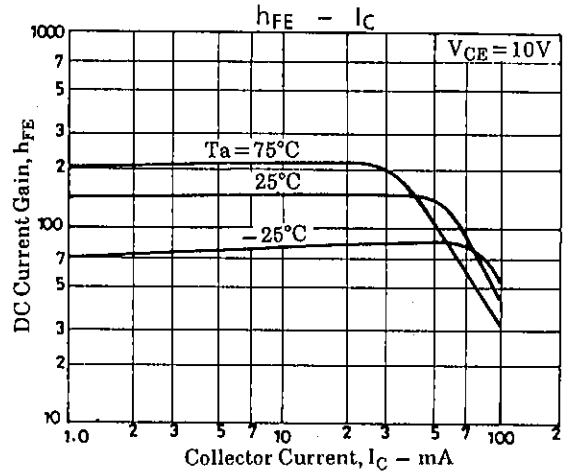
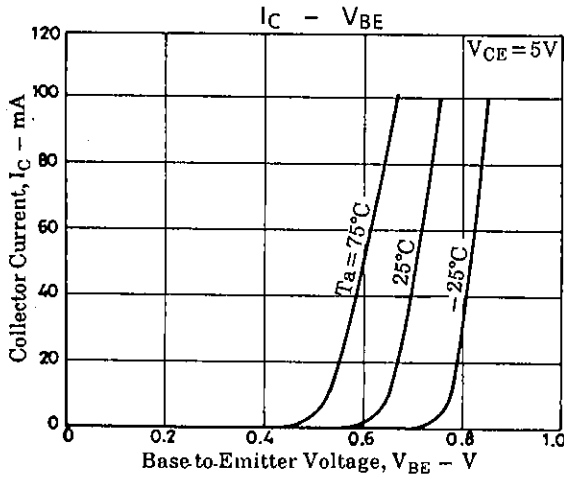
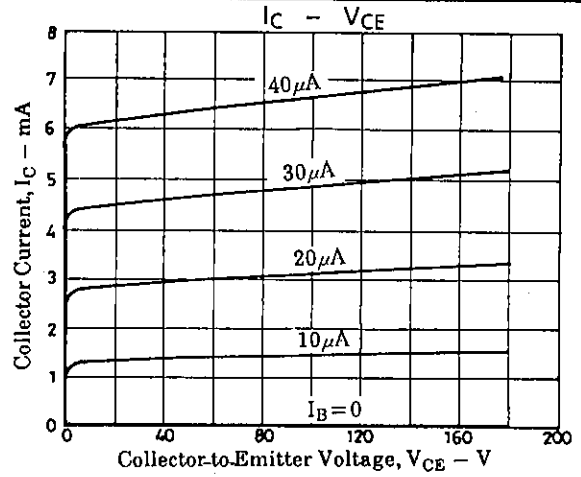
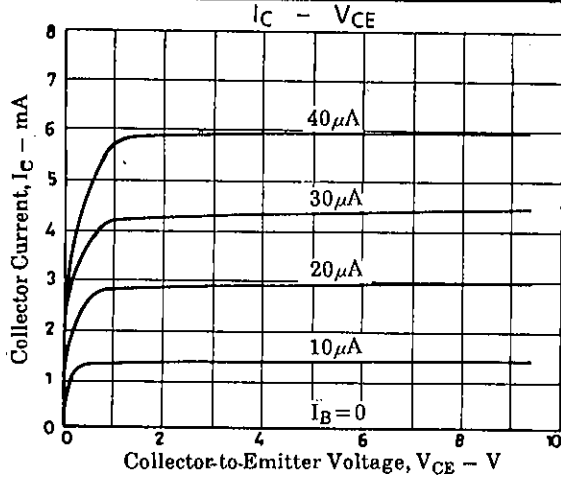
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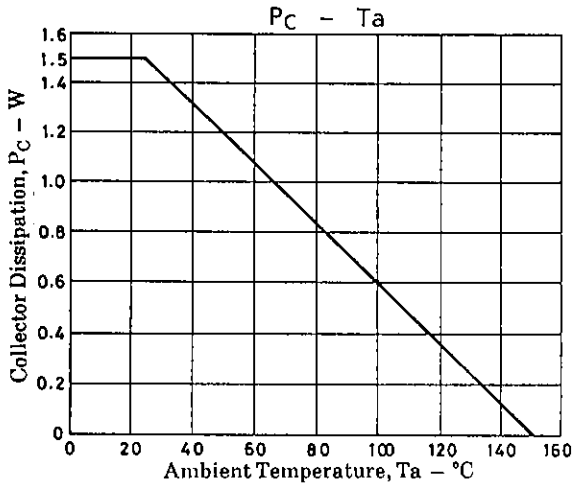
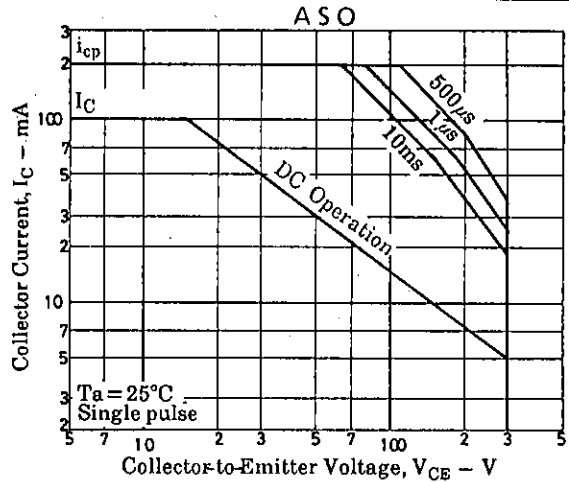
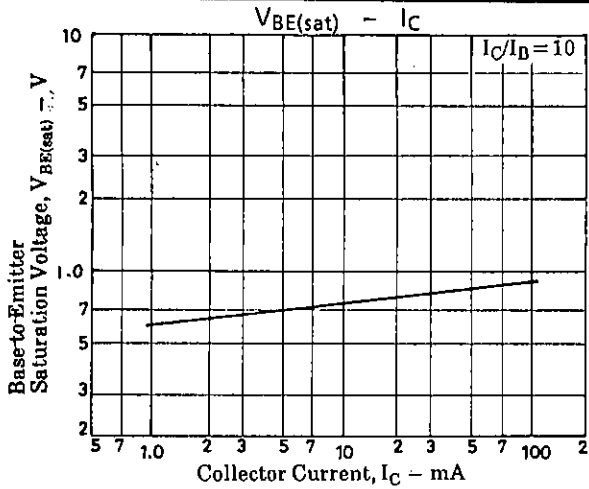
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